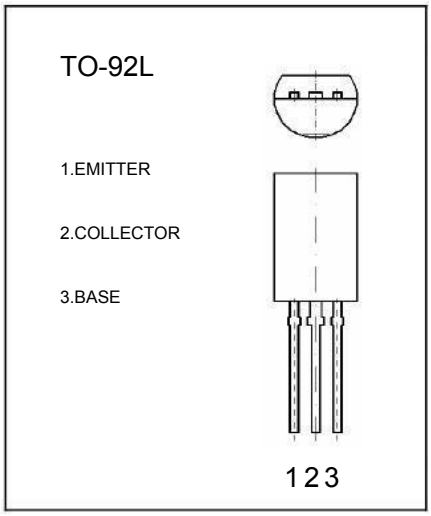
TO-92L Plastic-Encapsulate Transistors

A752

TRANSISTOR (PNP)



FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with C1407

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter			Units
V_{CBO}	Collector-Base Voltage		60	V
V_{CEO}	Collector-Emitter Voltage		50	V
V_{EBO}	Emitter-Base Voltage	5		V
I_C	Collector Current –Continuous	1.0		A
P_C	Collector Power Dissipation	1.0		W
T_J	Junction Temperature	135		℃
T_{stg}	Storage Temperature	-55-150		℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA , I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=2mA , I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10V, I_C=500mA	85		340	
DC current gain	$h_{FE(2)}$	V_{CE}=5V, I_C=1A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA		0.2	0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=500mA, I_B=50mA		0.85	1.2	V
Transition frequency	f_T	V_{CB}=10V, I_C=50mA		200		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	85-170	120-240	170-340